

# MOSFET – N-Channel, QFET

400 V, 4.5 A, 1.0 mΩ

## FQD6N40C

### Description

This N-Channel enhancement mode power MOSFET is produced using onsemi's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### Features

- 4.5 A, 400 V,  $R_{DS(on)} = 1.0 \text{ m}\Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 2.25 \text{ A}$
- Low Gate Charge (Typ. 16 nC)
- Low  $C_{rss}$  (Typ. 15 pF)
- 100% Avalanche Tested

### ABSOLUTE MAXIMUM RATINGS

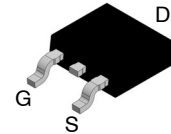
( $T_C = 25^\circ\text{C}$ , unless otherwise noted)

| Symbol         | Parameter                                                            | Ratings                                    | Unit                |
|----------------|----------------------------------------------------------------------|--------------------------------------------|---------------------|
| $V_{DSS}$      | Drain-Source Voltage                                                 | 400                                        | V                   |
| $I_D$          | Drain Current                                                        | – Continuous ( $T_C = 25^\circ\text{C}$ )  | 4.5                 |
|                |                                                                      | – Continuous ( $T_C = 100^\circ\text{C}$ ) | 2.7                 |
| $I_{DM}$       | Drain Current                                                        | – Pulsed (Note 1)                          | 18                  |
| $V_{GSS}$      | Gate-Source Voltage                                                  | $\pm 30$                                   | V                   |
| $E_{AS}$       | Single Pulsed Avalanche Energy (Note 2)                              | 270                                        | mJ                  |
| $I_{AR}$       | Avalanche Current (Note 1)                                           | 4.5                                        | A                   |
| $E_{AR}$       | Repetitive Avalanche Energy (Note 1)                                 | 4.8                                        | mJ                  |
| $dv/dt$        | Peak Diode Recovery $dv/dt$ (Note 3)                                 | 4.5                                        | V/ns                |
| $P_D$          | Power Dissipation ( $T_A = 25^\circ\text{C}$ ) *                     | 2.5                                        | W                   |
|                | Power Dissipation ( $T_C = 25^\circ\text{C}$ )                       | 48                                         | W                   |
|                | – Derate Above $25^\circ\text{C}$                                    | 0.38                                       | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                              | $-55$ to $+150$                            | $^\circ\text{C}$    |
| $T_L$          | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | 300                                        | $^\circ\text{C}$    |

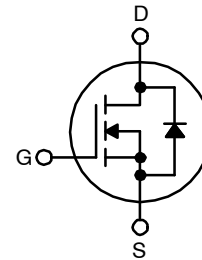
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

| Symbol          | Parameter                                                                             | Ratings | Unit                      |
|-----------------|---------------------------------------------------------------------------------------|---------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance Junction to Case, Max.                                             | 2.6     | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.            | 110     |                           |
|                 | Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max. | 50      |                           |



DPAK3 (TO-252 3 LD)  
CASE 369AS



N-Channel MOSFET

### MARKING DIAGRAM



&Z = Assembly Plant Code  
 &3 = 3-Digit Date Code (Year and Week)  
 &K = 2-Digits Lot Run Traceability Code  
 FQD6N40C = Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

# FQD6N40C

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

| Symbol | Parameter | Test Condition | Min | Typ | Max | Unit |
|--------|-----------|----------------|-----|-----|-----|------|
|--------|-----------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                      |                                           |                                                 |     |      |      |      |
|--------------------------------------|-------------------------------------------|-------------------------------------------------|-----|------|------|------|
| BV <sub>DSS</sub>                    | Drain-Source Breakdown Voltage            | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA  | 400 | –    | –    | V    |
| ΔBV <sub>DSS</sub> / ΔT <sub>J</sub> | Breakdown Voltage Temperature Coefficient | I <sub>D</sub> = 250 μA, Referenced to 25°C     | –   | 0.54 | –    | V/°C |
| I <sub>DSS</sub>                     | Zero Gate Voltage Drain Current           | V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V  | –   | –    | 1    | μA   |
|                                      |                                           | V <sub>DS</sub> = 320 V, T <sub>C</sub> = 125°C | –   | –    | 10   | μA   |
| I <sub>GSSF</sub>                    | Gate-Body Leakage Current, Forward        | V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V   | –   | –    | 100  | nA   |
| I <sub>GSSR</sub>                    | Gate-Body Leakage Current, Reverse        | V <sub>GS</sub> = –30 V, V <sub>DS</sub> = 0 V  | –   | –    | –100 | nA   |

### ON CHARACTERISTICS

|                     |                                   |                                                             |     |      |     |   |
|---------------------|-----------------------------------|-------------------------------------------------------------|-----|------|-----|---|
| V <sub>GS(th)</sub> | Gate Threshold Voltage            | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA | 2.0 | –    | 4.0 | V |
| R <sub>DS(on)</sub> | Static Drain-Source On-Resistance | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.25 A             | –   | 0.83 | 1   | Ω |
| g <sub>FS</sub>     | Forward Transconductance          | V <sub>DS</sub> = 40 V, I <sub>D</sub> = 2.25 A             | –   | 4.7  | –   | S |

### DYNAMIC CHARACTERISTICS

|                  |                              |                                                            |   |     |     |    |
|------------------|------------------------------|------------------------------------------------------------|---|-----|-----|----|
| C <sub>iss</sub> | Input Capacitance            | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz | – | 480 | 625 | pF |
| C <sub>oss</sub> | Output Capacitance           |                                                            | – | 80  | 105 | pF |
| C <sub>rss</sub> | Reverse Transfer Capacitance |                                                            | – | 15  | 20  | pF |

### SWITCHING CHARACTERISTICS

|                     |                     |                                                                                |   |     |     |    |
|---------------------|---------------------|--------------------------------------------------------------------------------|---|-----|-----|----|
| t <sub>d(on)</sub>  | Turn-On Delay Time  | V <sub>DD</sub> = 200 V, I <sub>D</sub> = 6 A, R <sub>G</sub> = 25 Ω (Note 4)  | – | 13  | 35  | ns |
| t <sub>r</sub>      | Turn-On Rise Time   |                                                                                | – | 65  | 140 | ns |
| t <sub>d(off)</sub> | Turn-Off Delay Time |                                                                                | – | 21  | 55  | ns |
| t <sub>f</sub>      | Turn-Off Fall Time  |                                                                                | – | 38  | 85  | ns |
| Q <sub>g</sub>      | Total Gate Charge   | V <sub>DS</sub> = 320 V, I <sub>D</sub> = 6 A, V <sub>GS</sub> = 10 V (Note 4) | – | 16  | 20  | nC |
| Q <sub>gs</sub>     | Gate-Source Charge  |                                                                                | – | 2.3 | –   | nC |
| Q <sub>gd</sub>     | Gate-Drain Charge   |                                                                                | – | 8.2 | –   | nC |

### DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

|                 |                                                       |                                                                                 |   |     |     |    |
|-----------------|-------------------------------------------------------|---------------------------------------------------------------------------------|---|-----|-----|----|
| I <sub>S</sub>  | Maximum Continuous Drain–Source Diode Forward Current |                                                                                 | – | –   | 4.5 | A  |
| I <sub>SM</sub> | Maximum Pulsed Drain–Source Diode Forward Current     |                                                                                 | – | –   | 18  | A  |
| V <sub>SD</sub> | Drain–Source Diode Forward Voltage                    | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 4.5 A                                   | – | –   | 1.4 | V  |
| t <sub>rr</sub> | Reverse Recovery Time                                 | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 6 A,<br>dI <sub>F</sub> / dt = 100 A/μs | – | 230 | –   | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                               |                                                                                 | – | 1.7 | –   | μC |

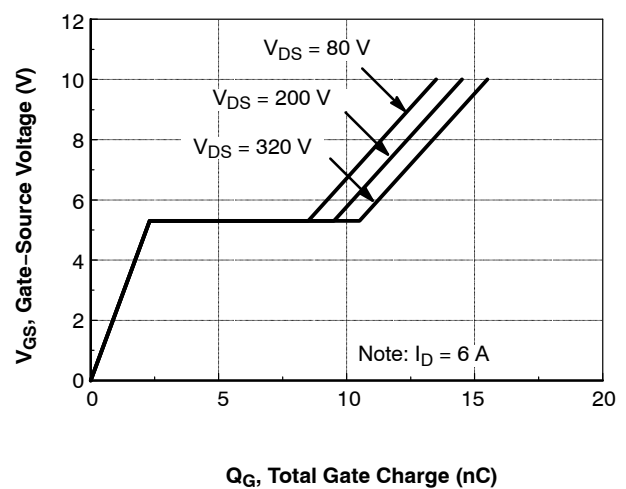
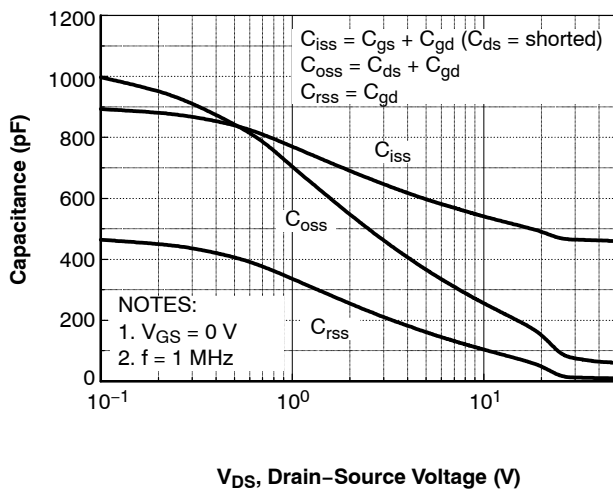
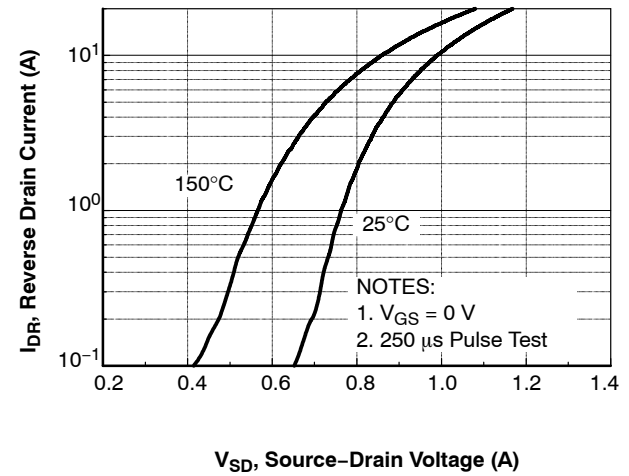
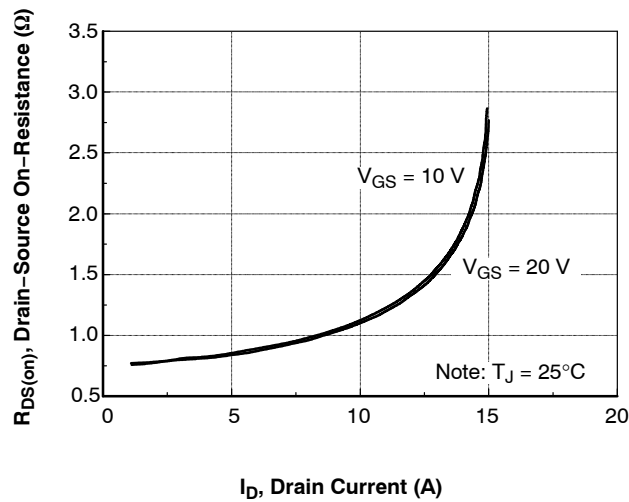
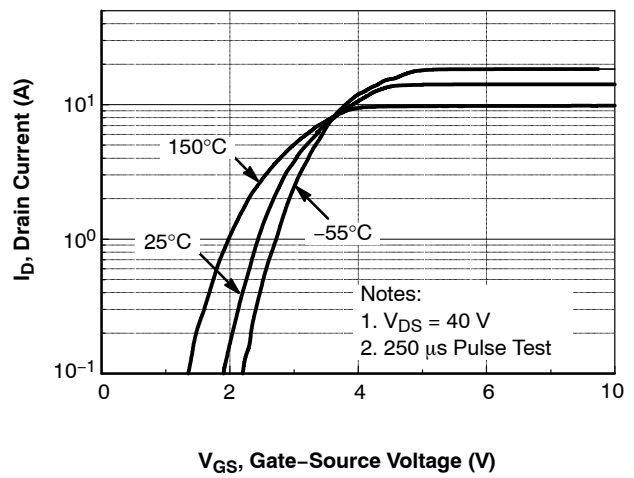
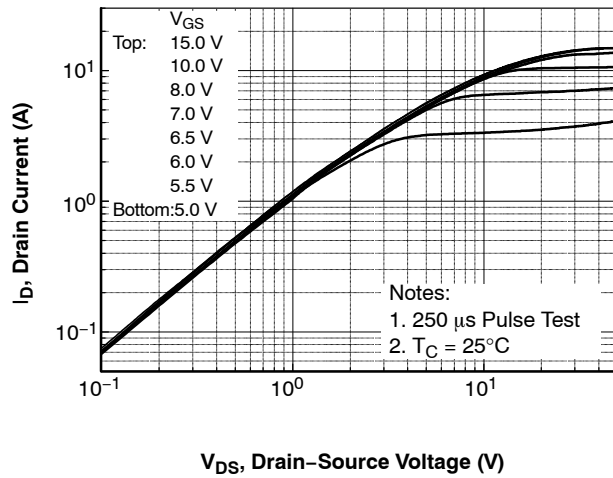
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### NOTES:

1. Repetitive Rating: Pulse-width limited by maximum junction temperature.
2. L = 13.7 mH, I<sub>AS</sub> = 6 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.
3. I<sub>SD</sub> ≤ 6 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C.
4. Essentially independent of operating temperature.

# FQD6N40C

## TYPICAL CHARACTERISTICS



# FQD6N40C

## TYPICAL CHARACTERISTICS (continued)

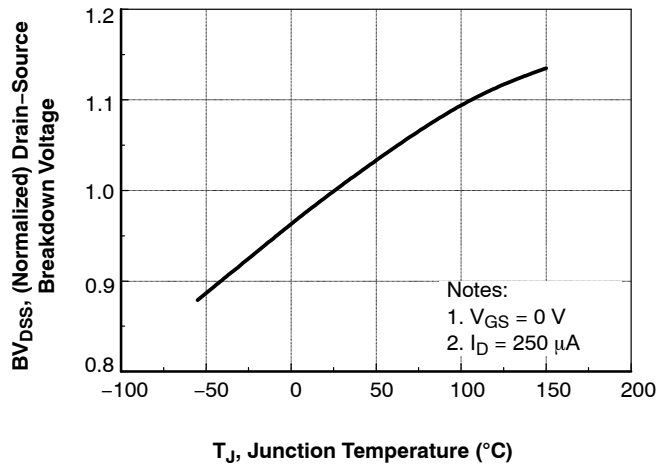


Figure 7. Breakdown Voltage Variation vs. Temperature

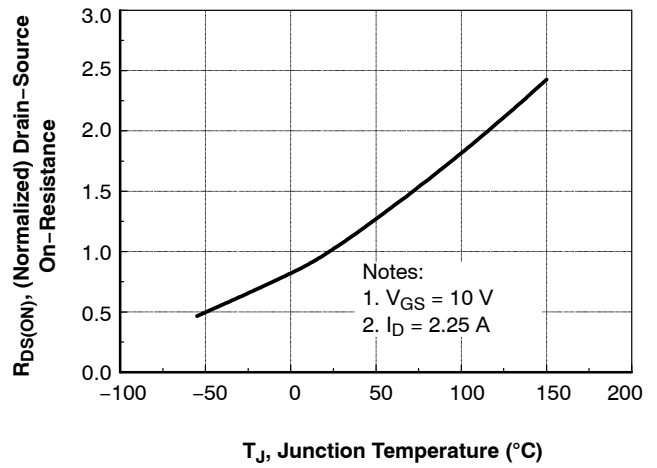


Figure 8. On-Resistance Variation vs. Temperature

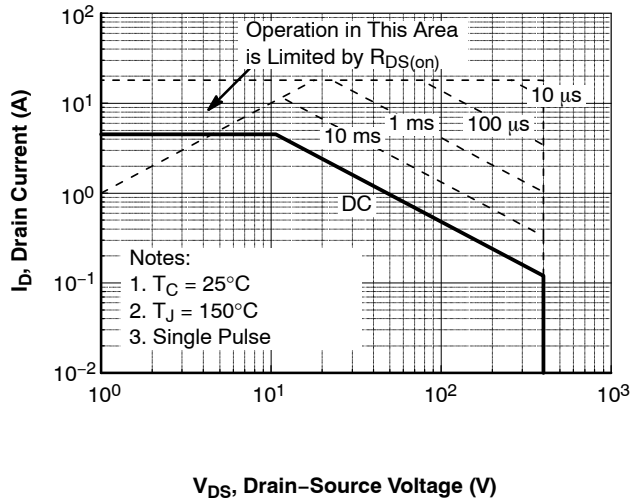


Figure 9. Maximum Safe Operating Area

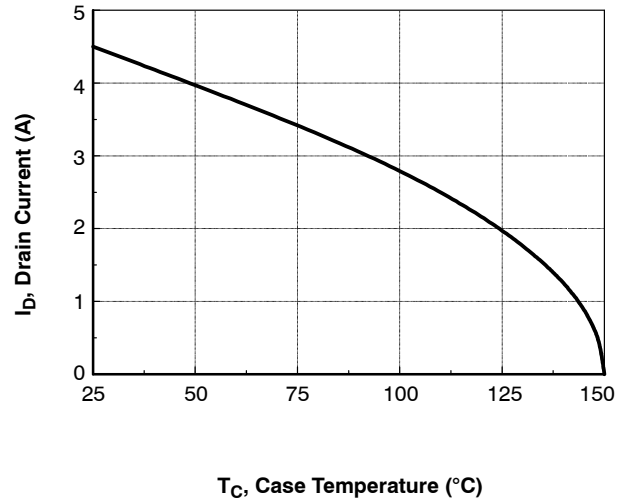


Figure 10. Maximum Drain Current vs. Case Temperature

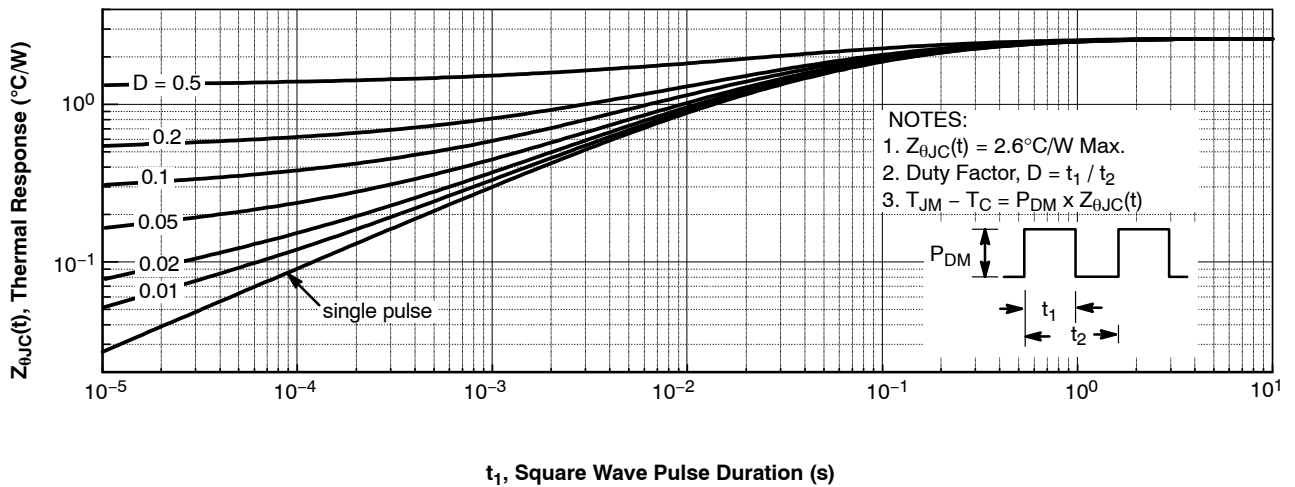
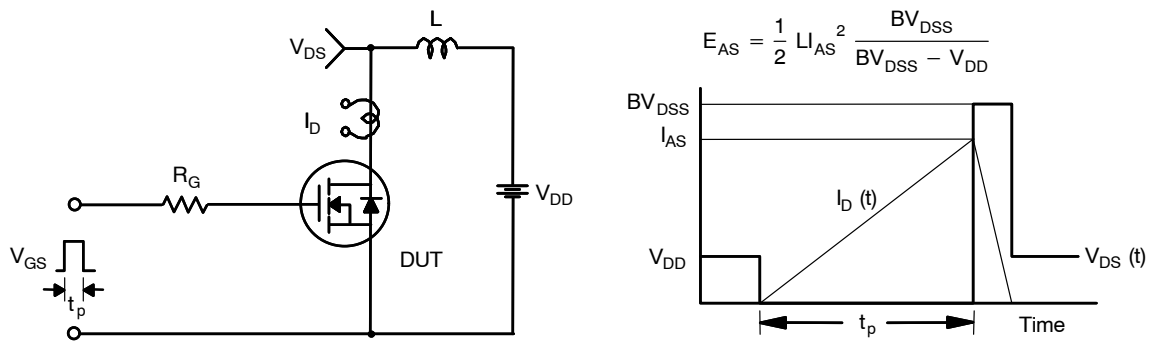
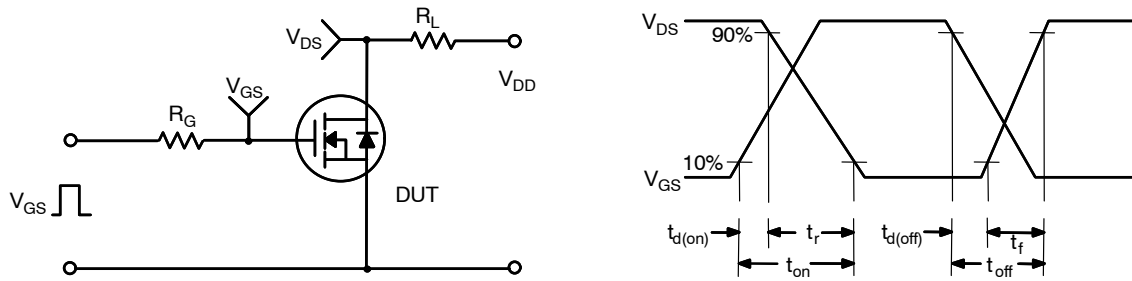
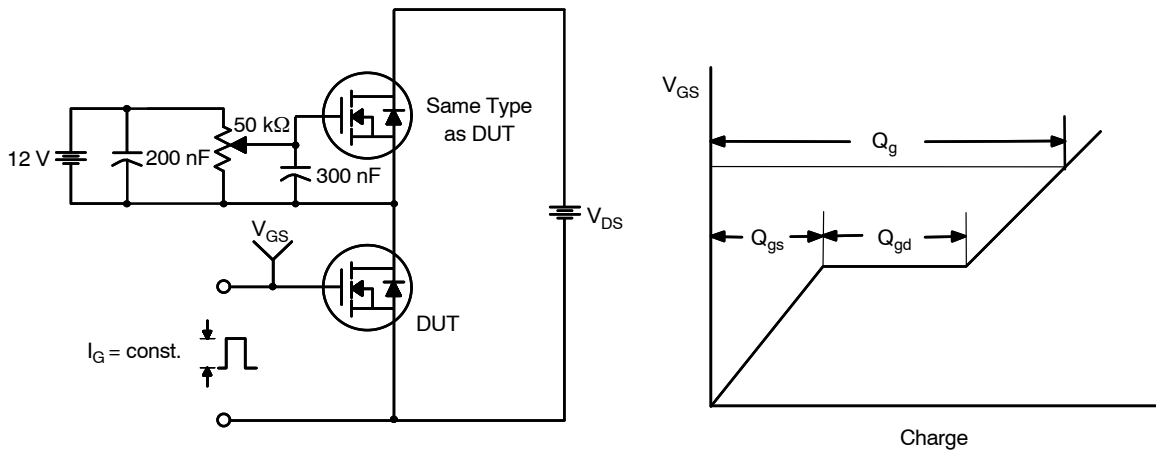


Figure 11. Transient Thermal Response Curve

## FQD6N40C



## FQD6N40C

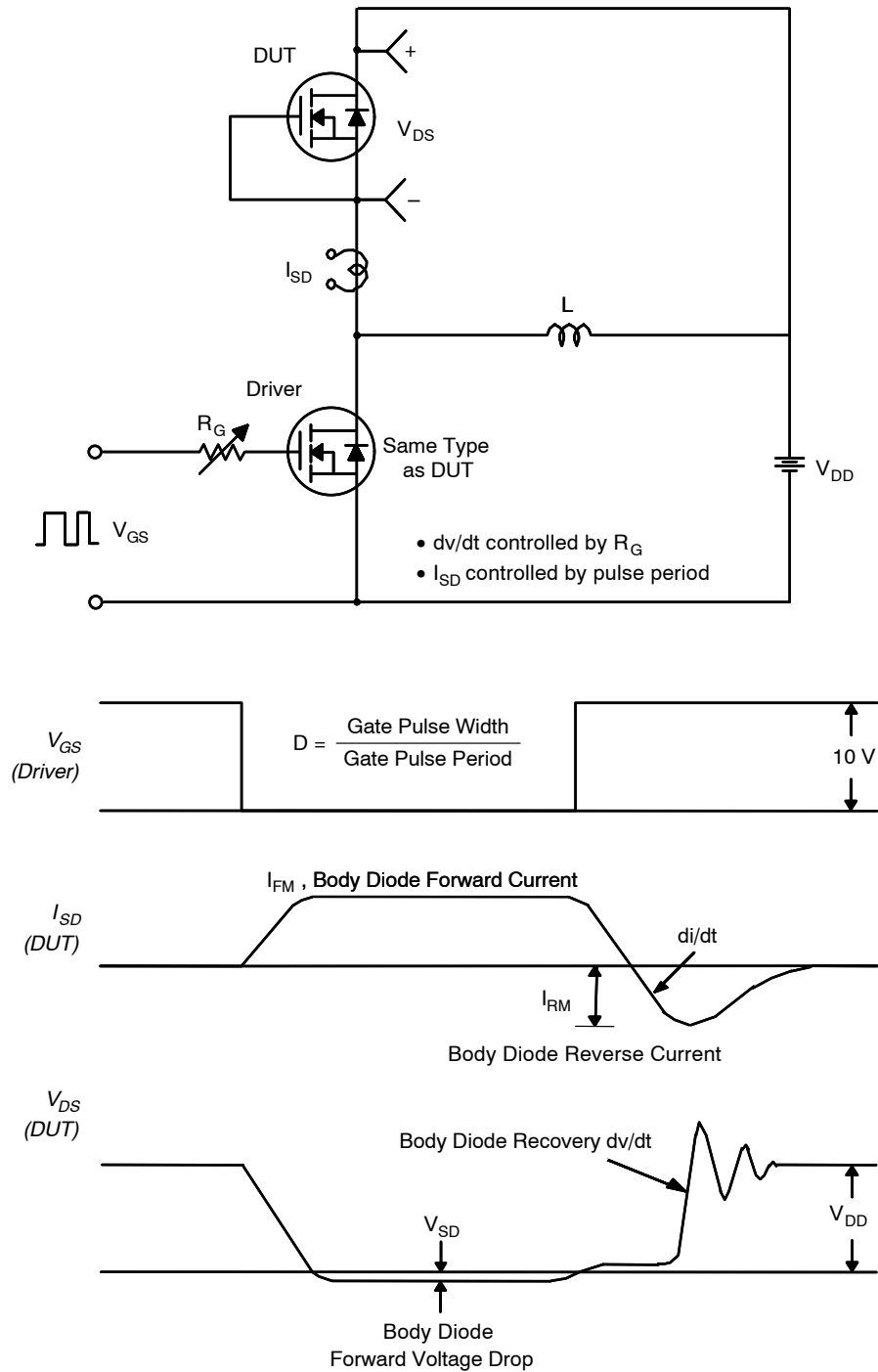
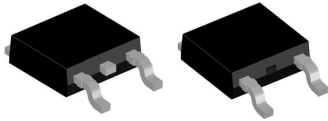


Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

### PACKAGE MARKING AND ORDERING INFORMATION

| Device     | Device Marking | Package             | Reel Size | Tape Width | Shipping <sup>†</sup> |
|------------|----------------|---------------------|-----------|------------|-----------------------|
| FQD6N40CTM | FQD6N40C       | DPAK3 (TO-252 3 LD) | 330 mm    | 16 mm      | 2,500 / Tape & Reel   |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).


**DPAK3 6.10x6.54x2.29, 4.57P**  
**CASE 369AS**  
**ISSUE B**

DATE 20 DEC 2023



NON-DIODE PRODUCTS VERSION



NON-DIODE PRODUCTS VERSION



NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE F, VARIATION AA.

B) ALL DIMENSIONS ARE IN MILLIMETERS.

C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2018.

D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.

E) FOR DIODE PRODUCTS, L4 IS 0.25 MM MAX PLASTIC BODY STUB WITHOUT CENTER LEAD.

F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.

G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TD228P991X239-3N.


**LAND PATTERN RECOMMENDATION**

\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

| DIM | MILLIMETERS |      |       |
|-----|-------------|------|-------|
|     | MIN.        | NDM. | MAX.  |
| A   | 2.18        | 2.29 | 2.39  |
| A1  | 0.00        | -    | 0.127 |
| b   | 0.64        | 0.77 | 0.89  |
| b2  | 0.76        | 0.95 | 1.14  |
| b3  | 5.21        | 5.34 | 5.46  |
| c   | 0.45        | 0.53 | 0.61  |
| c2  | 0.45        | 0.52 | 0.58  |
| D   | 5.97        | 6.10 | 6.22  |
| D1  | 5.21        | ---  | ---   |
| E   | 6.35        | 6.54 | 6.73  |
| E1  | 4.32        | ---  | ---   |
| e   | 2.286 BSC   |      |       |
| e1  | 4.572 BSC   |      |       |
| H   | 9.40        | 9.91 | 10.41 |
| L   | 1.40        | 1.59 | 1.78  |
| L1  | 2.90 REF    |      |       |
| L2  | 0.51 BSC    |      |       |
| L3  | 0.89        | 1.08 | 1.27  |
| L4  | ---         | ---  | 1.02  |
| θ   | 0°          | ---  | 10°   |

**GENERIC MARKING DIAGRAM\***


\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Assembly Lot Code

|                         |                                    |                                                                                                                                                                                  |
|-------------------------|------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| <b>DOCUMENT NUMBER:</b> | <b>98AON13810G</b>                 | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| <b>DESCRIPTION:</b>     | <b>DPAK3 6.10x6.54x2.29, 4.57P</b> | <b>PAGE 1 OF 1</b>                                                                                                                                                               |

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at  
[www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)